

# Atsushi Tsurumaki-Fukuchi

## List of Publications by Citations

**Source:** <https://exaly.com/author-pdf/8392296/atsushi-tsurumaki-fukuchi-publications-by-citations.pdf>

**Version:** 2024-04-27

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

32  
papers

401  
citations

9  
h-index

19  
g-index

45  
ext. papers

459  
ext. citations

3.5  
avg, IF

3.53  
L-index

#	Paper	IF	Citations
32	Impact of Bi Deficiencies on Ferroelectric Resistive Switching Characteristics Observed at p-Type Schottky-Like Pt/Bi1-xFeO3 Interfaces. <i>Advanced Functional Materials</i> , <b>2012</b> , 22, 1040-1047	15.6	153
31	Switching operation and degradation of resistive random access memory composed of tungsten oxide and copper investigated using in-situ TEM. <i>Scientific Reports</i> , <b>2015</b> , 5, 17103	4.9	44
30	Strong Surface-Termination Effect on Electroresistance in Ferroelectric Tunnel Junctions. <i>Advanced Functional Materials</i> , <b>2015</b> , 25, 2708-2714	15.6	39
29	Resistive switching artificially induced in a dielectric/ferroelectric composite diode. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 152903	3.4	39
28	Probing electrochemistry at the nanoscale: in situ TEM and STM characterizations of conducting filaments in memristive devices. <i>Journal of Electroceramics</i> , <b>2017</b> , 39, 73-93	1.5	22
27	Multilevel recording in Bi-deficient Pt/BFO/SRO heterostructures based on ferroelectric resistive switching targeting high-density information storage in nonvolatile memories. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 263502	3.4	18
26	Smooth Interfacial Scavenging for Resistive Switching Oxide via the Formation of Highly Uniform Layers of Amorphous TaO. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 5609-5617	9.5	16
25	Microstructural transitions in resistive random access memory composed of molybdenum oxide with copper during switching cycles. <i>Nanoscale</i> , <b>2016</b> , 8, 14754-66	7.7	13
24	Modeling of hysteretic Schottky diode-like conduction in Pt/BiFeO3/SrRuO3 switches. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 082904	3.4	10
23	Ca doping dependence of resistive switching characteristics in ferroelectric capacitors comprising Ca-doped BiFeO3. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 204104	2.5	8
22	Resistive switching characteristics in dielectric/ferroelectric composite devices improved by post-thermal annealing at relatively low temperature. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 092903	3.4	6
21	Observation of Conductive Filament in CBRAM at Switching Moment. <i>ECS Transactions</i> , <b>2017</b> , 80, 895-902		5
20	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 214305	2.5	5
19	Stable and Tunable Current-Induced Phase Transition in Epitaxial Thin Films of CaRuO. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 28368-28374	9.5	3
18	Fabrication and evaluation of series-triple quantum dots by thermal oxidation of silicon nanowire. <i>AIP Advances</i> , <b>2015</b> , 5, 117144	1.5	3
17	Initial states and analog switching behaviors of two major tantalum oxide resistive memories. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, 044004	1.4	2
16	Tunnel magnetocapacitance in Fe/MgF2 single nanogranular layered films. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 082401	3.4	2

15	In-situ Electron Microscopy of Cu Movement in MoO <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> Bilayer CBRAM during Cyclic Switching. <i>ECS Transactions</i> , <b>2017</b> , 80, 903-910	1	2
14	Resistive Switching Memory Based on Ferroelectric Polarization Reversal at Schottky-like BiFeO <sub>3</sub> Interfaces. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1430, 31		2
13	Periodic Coulomb blockade oscillations observed in single-layered Fe nanodot array. <i>Thin Solid Films</i> , <b>2020</b> , 704, 138012	2.2	2
12	Analog memory characteristics of 1T1R MoO <sub>x</sub> resistive random access memory <b>2016</b> ,		2
11	Filamentary switching of ReRAM investigated by in-situ TEM. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SG0803	1.4	1
10	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO <sub>3</sub> /Pt. <i>MRS Advances</i> , <b>2018</b> , 3, 1925-1930	0.7	1
9	In-situ TEM of Nanoscale ReRAM Devices. <i>Vacuum and Surface Science</i> , <b>2018</b> , 61, 766-771	0	1
8	Charge-offset stability of single-electron devices based on single-layered Fe nanodot array. <i>AIP Advances</i> , <b>2021</b> , 11, 035230	1.5	1
7	Capacitance evaluation of compact silicon triple quantum dots by simultaneous gate voltage sweeping. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 234502	2.5	1
6	Controlled Current Transport in Pt/Nb:SrTiO <sub>3</sub> Junctions via Insertion of Uniform Thin Layers of TaO <sub>x</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2019</b> , 13, 1900136	2.5	0
5	Initialization process of Cu-based WO <sub>x</sub> conductive bridge RAM investigated via in situ transmission electron microscopy. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, S11E01	1.4	
4	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO <sub>3</sub> /Pt □ CORRIGENDUM. <i>MRS Advances</i> , <b>2018</b> , 3, 2075-2075	0.7	
3	Superconducting weak link generated at atomic steps on a substrate in a YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> ultrathin film. <i>Physica C: Superconductivity and Its Applications</i> , <b>2010</b> , 470, S863-S864	1.3	
2	Probing Electrochemistry at the Nanoscale: In Situ TEM and STM Characterizations of Conducting Filaments in Memristive Devices. <i>Kluwer International Series in Electronic Materials: Science and Technology</i> , <b>2022</b> , 87-120		
1	Initial electrical properties of tantalum oxide resistive memories influenced by oxygen defect concentrations. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SCCE03	1.4	